

2STR2230

Low voltage fast-switching PNP power transistor

General features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits
- In compliance with the 2002/93/EC European Directive

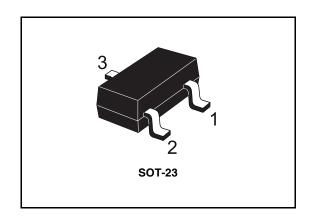
Description

The 2STR2230 is a PNP transistor manufactured using new "PB-HCD" (Power Bipolar High Current Density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

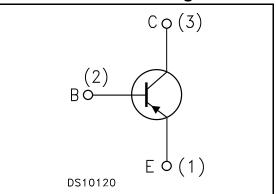
The complementary NPN is the 2STR1230.

Applications

- LED
- Motherboard & hard disk drive
- Mobile equipment
- Battery charger
- Voltage regulation



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
2STR2230	230	SOT-23	Tape & reel

November 2006 Rev 3 1/9

Contents

1	Electrical ratings 3
2	Electrical characteristics 4
	2.1 Electrical characteristics (curves)
3	Package mechanical data
4	Revision history 8



2STR2230 Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{CE} = 0)	-30	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-30	V
V _{EBO}	Emitter-base voltage (I _C = 0)	-5	V
I _C	Collector current	-1.5	Α
I _{CM}	Collector peak current (t _P < 5ms)	-3	Α
P _{tot}	Total dissipation at T _{amb} = 25°C	0.5	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-amb max	250	°C/W

(1) Device mounted on PCB area of $1\,\mathrm{cm}^2$

Electrical characteristics 2STR2230

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E =0)	V _{CB} = -30V			-0.1	μА
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = -4V			-0.1	μА
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100μA	-30			V
V _{(BR)CEO} (2)	Collector-emitter breakdown voltage (I _B = 0)	I _C = -10mA	-30			V
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = -100μA	-5			V
V (2)	0 11	$I_C = -0.1A$ $I_B = -1mA$			-0.17	V
V _{CE(sat)} (2)	Collector-emitter saturation voltage	$I_C = -1A$ $I_B = -100mA$		-0.25	-0.45	V
		$I_C = -2A$ $I_B = -200 \text{mA}$		-0.42	-0.8	V
V _{BE(sat)} (2)	Base-emitter saturation voltage	$I_{C} = -1A$ $I_{B} = -100mA$		-0.9	-1.25	V
		$I_C = -50 \text{mA}$ $V_{CE} = -2 \text{V}$	210			
h _{FF} ⁽²⁾	DC current gain	$I_C = -0.5A$ $V_{CE} = -2V$	170	280	560	
''FE`'		$I_C = -1A$ $V_{CE} = -2V$	100			
		$I_C = -1.5A$ $V_{CE} = -2V$	70			
f _T	Transition frequency	$I_C = -0.1A$ $V_{CE} = -5V$ $f = 100MHz$	100			MHz
C _{CBO}	Collector-base capacitance	$I_E = 0$ $V_{CB} = -10V$ f = 1MHz		10		pF
	Resistive load	I _C = -1.5A V _{CC} = -10V				
t _{on}	Turn-on time	$I_{B1} = -I_{B2} = -150 \text{mA}$		74		ns
t _{off}	Turn-off time	.B1 .B2		200		ns

Note (2) Pulsed duration = 300 μ s, duty cycle \leq 1.5%

4/9

2.1 Electrical characteristics (curves)

Figure 1. DC current gain

100

T_J=25 °C

100

V_{CE}=2V

Figure 2. Collector-emitter saturation voltage

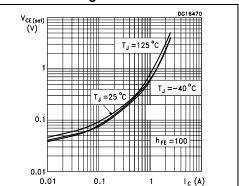
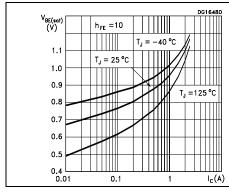


Figure 3. Base-emitter saturation voltage

Figure 4. Resistive load switching time



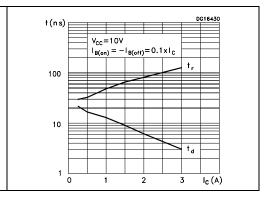
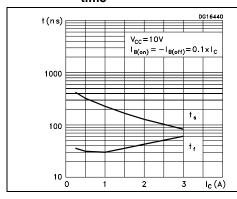
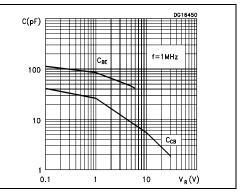


Figure 5. Resistive load switching time

Figure 6. Capacitance





57

3 Package mechanical data

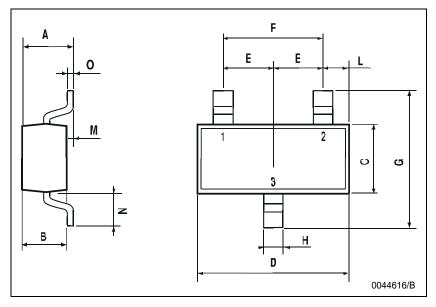
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

477

6/9

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
Е	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
Н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
М	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7



57

Revision history 2STR2230

4 Revision history

Table 4. Revision history

Date	Revision	Changes	
18-Jul-2006	1	Initial release	
31-Oct-2006	2	New graphics	
07-Nov-2006	3	Maturity changed from preliminary to full.	

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

577

9/9